

Schottky Barrier Rectifiers

Using the Schottky Barrier principle with a Molybdenum barrier metal. These state-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity protection diodes.

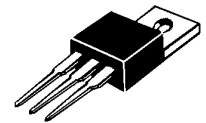
Features

- * Low Forward Voltage.
- * Low Switching noise.
- * High Current Capacity
- * Guarantee Reverse Avalanche.
- * Guard-Ring for Stress Protection.
- * Low Power Loss & High efficiency.
- * 150°C Operating Junction Temperature
- * Low Stored Charge Majority Carrier Conduction.
- * Plastic Material used Carries Underwriters Laboratory Flammability Classification 94V-O
- * **Pb free**
- * **In compliance with EU RoHs directives**

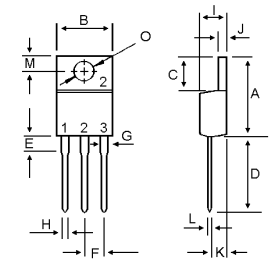


SCHOTTKY BARRIER RECTIFIERS

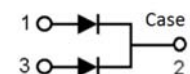
**20 AMPERES
45 VOLTS**



TO-220AB



DIM	MILLIMETERS	
	MIN	MAX
A	14.68	16.00
B	9.78	10.42
C	5.02	6.60
D	13.00	14.62
E	3.10	4.19
F	2.41	2.67
G	1.10	1.67
H	0.69	1.01
I	4.22	4.98
J	1.14	1.40
K	2.20	3.30
L	0.28	0.61
M	2.48	3.00
O	3.50	4.00



MAXIMUM RATINGS

Characteristic	Symbol	S20C45C	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	45	V
RMS Reverse Voltage	$V_{R(RMS)}$	32	V
Average Rectifier Forward Current (per diode) Total Device (Rated V_R , $T_C=100^\circ\text{C}$)	$I_{F(AV)}$	10 20	A
Peak Repetitive Forward Current (Rate V_R , Square Wave, 20kHz)	I_{FM}	20	A
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions halfwave, single phase, 60Hz)	I_{FSM}	200	A
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Maximum Instantaneous Forward Voltage ($I_F=10\text{ Amp } T_C=25^\circ\text{C}$) ($I_F=10\text{ Amp } T_C=125^\circ\text{C}$)	V_F	---	0.52 0.47	0.60 ---	V
Maximum Instantaneous Reverse Current (Rated DC Voltage, $T_C=25^\circ\text{C}$) (Rated DC Voltage, $T_C=125^\circ\text{C}$)	I_R	---	0.04 30	0.1 ---	mA
Typical Thermal Resistance junction to case	$R_{\theta jc}$		3.8		$^\circ\text{C}/\text{w}$

FIG-1 FORWARD CURRENT DERATING CURVE

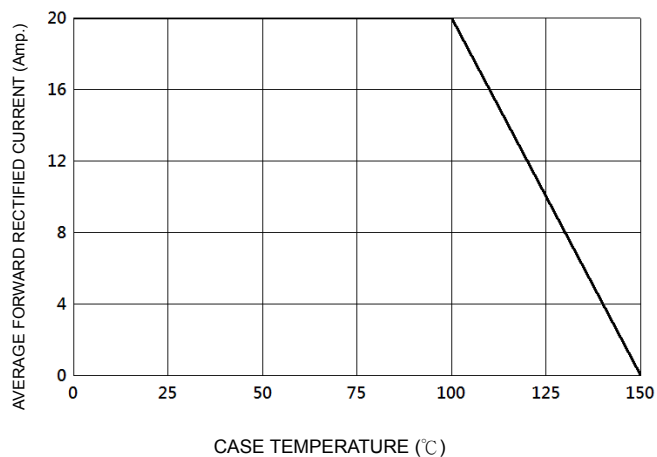


FIG-2 TYPICAL FORWARD CHARACTERISTICS

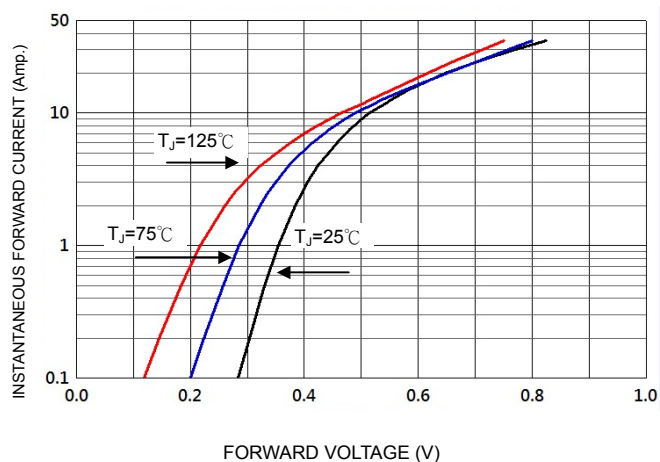


FIG-3 TYPICAL REVERSE CHARACTERISTICS

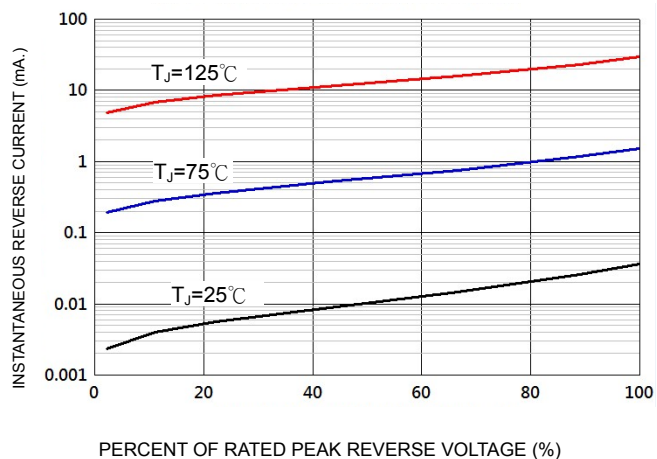


FIG-4 TYPICAL JUNCTION CAPACITANCE

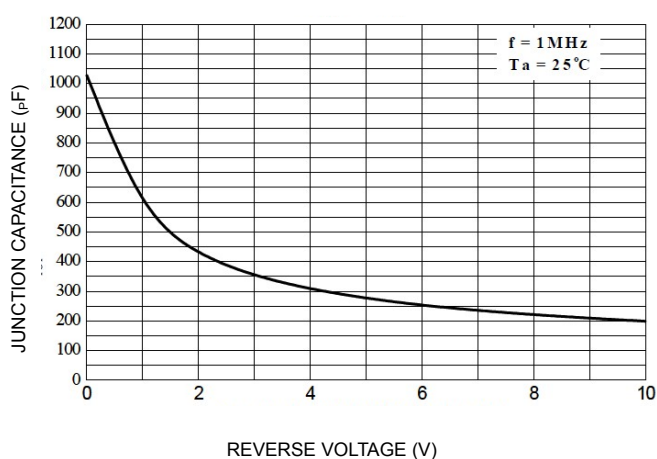
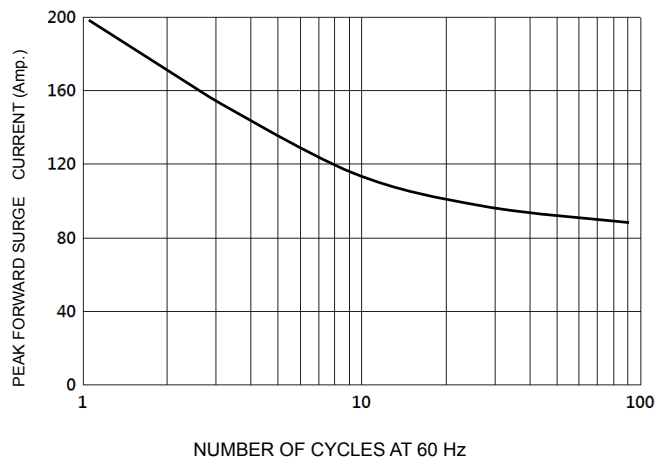


FIG-5 PEAK FORWARD SURGE CURRENT



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